## NTJD1155L

## Power MOSFET

## 8 V, $\pm 1.3$ A, High Side Load Switch with Level-Shift, P-Channel SC-88

The NTJD1155L integrates a P and N -Channel MOSFET in a single package. This device is particularly suited for portable electronic equipment where low control signals, low battery voltages and high load currents are needed. The $\mathrm{P}-$ Channel device is specifically designed as a load switch using ON Semiconductor state-of-the-art trench technology. The N -Channel, with an external resistor (R1), functions as a level-shift to drive the P -Channel. The N -Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V . The NTJD1155L operates on supply lines from 1.8 to 8.0 V and can drive loads up to 1.3 A with 8.0 V applied to both $\mathrm{V}_{\mathrm{IN}}$ and $\mathrm{V}_{\mathrm{ON} / \mathrm{OFF}}$

## Features

- Extremely Low $\mathrm{R}_{\mathrm{DS}(\text { on) }} \mathrm{P}-$ Channel Load Switch MOSFET
- Level Shift MOSFET is ESD Protected
- Low Profile, Small Footprint Package
- $\mathrm{V}_{\mathrm{IN}}$ Range 1.8 to 8.0 V
- ON/OFF Range 1.5 to 8.0 V
- ESD Rating of 3000 V
- $\mathrm{Pb}-$ Free Package is Available

MAXIMUM RATINGS $\left(T_{J}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Rating |  |  | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Input Voltage (V $\mathrm{V}_{\text {DS }}$, P-Ch) |  |  | $\mathrm{V}_{\text {IN }}$ | 8.0 | V |
| ON/OFF Voltage (VGS, N-Ch) |  |  | $\mathrm{V}_{\text {ON/OFF }}$ | 8.0 | V |
| Continuous Load Current (Note 1) | Steady State | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | L | $\pm 1.3$ | A |
|  |  | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ |  | $\pm 0.9$ |  |
| Power Dissipation (Note 1) | Steady State | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 0.40 | W |
|  |  | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ |  | 0.20 |  |
| Pulsed Load Current |  | $10 \mu \mathrm{~s}$ | ILM | $\pm 3.9$ | A |
| Operating Junction and Storage Temperature |  |  | $\begin{gathered} \hline \mathrm{T}_{\mathrm{J},} \\ \mathrm{~T}_{\text {STG }} \end{gathered}$ | $\begin{gathered} -55 \text { to } \\ 150 \end{gathered}$ | ${ }^{\circ} \mathrm{C}$ |
| Source Current (Body Diode) |  |  | Is | -0.4 | A |
| $\begin{aligned} & \text { ESD Rating, MIL-STD-883D HBM } \\ & (100 \mathrm{pF}, 1.5 \mathrm{k} \Omega) \end{aligned}$ |  |  | ESD | 3.0 | kV |
| Lead Temperature for Soldering Purposes ( $1 / 8^{\prime \prime}$ from case for 10 s ) |  |  | TL | 260 | ${ }^{\circ} \mathrm{C}$ |

Maximum ratings are those values beyond which device damage can occur Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## THERMAL RESISTANCE RATINGS

| Rating | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Junction-to-Ambient - Steady State (Note 1) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 320 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction-to-Foot - Steady State (Note 1) | $\mathrm{R}_{\theta \mathrm{JF}}$ | 220 |  |

[^0](Cu area $=1.127$ in sq [1 oz] including traces).

ON Semiconductor ${ }^{\text {® }}$
http://onseml.com

| $\mathbf{V}_{\text {(BR)DSS }}$ | $\mathbf{R}_{\mathbf{D S} \text { (on) }}$ TYP | $\mathbf{I}_{\mathbf{D}} \mathbf{M A X}$ |
| :---: | :---: | :---: |
| 8.0 V | $130 \mathrm{~m} \Omega @-4.5 \mathrm{~V}$ | $\pm 1.3 \mathrm{~A}$ |
|  | $170 \mathrm{~m} \Omega @-2.5 \mathrm{~V}$ |  |
|  | $260 \mathrm{~m} \Omega @-1.8 \mathrm{~V}$ |  |

SIMPLIFIED SCHEMATIC


| SC-88 |  |
| :---: | :---: |
| (SOT-363) |  |
| 1 | CASE 419B |
| STYLE 30 |  |

TE = Device Code
M = Date Code

- $\quad$ Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT
D1/G2 G1 S2


ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| NTJD1155LT1 | SC-88 | $3000 /$ Tape \& Reel |
| NTJD1155LT1G | SC-88 <br> (Pb-Free) | 3000/Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{J}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic | Symbol | Test Condition |  | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |  |  |
| Q2 Drain-to-Source Breakdown Voltage | $\mathrm{V}_{\text {IN }}$ | $\mathrm{V}_{\mathrm{GS} 2}=0 \mathrm{~V}, \mathrm{l}_{\mathrm{D} 2}=250 \mu \mathrm{~A}$ |  | -8.0 |  |  | V |
| Forward Leakage Current | $\mathrm{I}_{\mathrm{FL}}$ | $\begin{gathered} \mathrm{V}_{\mathrm{GS} 1}=0 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{DS} 2}=-8.0 \mathrm{~V} \end{gathered}$ | $\mathrm{T}_{J}=25^{\circ} \mathrm{C}$ |  |  | 1.0 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{T}_{\mathrm{J}}=125^{\circ} \mathrm{C}$ |  |  | 10 |  |
| Q1 Gate-to-Source Leakage Current | IGSS | $\mathrm{V}_{\mathrm{DS} 1}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS} 1}= \pm 8.0 \mathrm{~V}$ |  |  |  | $\pm 100$ | nA |
| Q1 Diode Forward On-Voltage | $\mathrm{V}_{\text {SD }}$ | $\mathrm{I}_{\mathrm{S}}=-0.4 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS} 1}=0 \mathrm{~V}$ |  |  | -0.8 | -1.1 | V |

ON CHARACTERISTICS

| ON/OFF Voltage |  |  |  | 1.5 |  | 8.0 | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Q1 Gate Threshold Voltage | $\mathrm{V}_{\text {GS1 (th) }}$ | $\mathrm{V}_{\mathrm{GS} 1}=\mathrm{V}_{\mathrm{DS} 1}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |  | 0.4 |  | 1.0 | V |
| Input Voltage | $\mathrm{V}_{\text {IN }}$ | $\mathrm{V}_{\mathrm{GS} 1}=\mathrm{V}_{\mathrm{DS} 1}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |  | 1.8 |  | 8.0 | V |
| Q2 Drain-to-Source On Resistance | $\mathrm{R}_{\mathrm{DS} \text { (on) }}$ | $\mathrm{V}_{\text {ON/OFF }}=1.5 \mathrm{~V}$ | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=4.5 \mathrm{~V} \\ \mathrm{I}_{\mathrm{L}}=1.2 \mathrm{~A} \end{gathered}$ |  | 130 | 175 | $\mathrm{m} \Omega$ |
|  |  |  | $\begin{aligned} & \mathrm{V}_{I N}=2.5 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{L}}=1.0 \mathrm{~A} \end{aligned}$ |  | 170 | 220 |  |
|  |  |  | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=1.8 \mathrm{~V} \\ \mathrm{I}_{\mathrm{L}}=0.7 \mathrm{~A} \end{gathered}$ |  | 260 | 320 |  |
| Load Current | $I_{L}$ | $\begin{gathered} \mathrm{V}_{\mathrm{DROP}} \leq 0.2 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=5.0 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{ON} / \mathrm{OFF}}=1.5 \mathrm{~V} \end{gathered}$ |  | 1.0 |  |  | A |
|  |  | $\begin{gathered} \mathrm{V}_{\text {DROP }} \leq 0.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=2.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{ON} / \mathrm{OFF}}=1.5 \mathrm{~V} \end{gathered}$ |  | 1.0 |  |  |  |



Figure 1. Load Switch Application

| Components | Description | Values |
| :---: | :--- | :--- |
| R1 | Pullup Resistor | Typical $10 \mathrm{k} \Omega$ to $1.0 \Omega^{\star}$ |
| R2 | Optional Slew-Rate Control | Typical 0 to $100 \mathrm{k} \Omega^{\star}$ |
| $\mathrm{C}_{\mathrm{O}}, \mathrm{C}_{\mathrm{l}}$ | Output Capacitance | Usually $<1.0 \mu \mathrm{~F}$ |
| C1 | Optional In-Rush Current Control | Typical $\leq 1000 \mathrm{pF}$ |

[^1]TYPICAL PERFORMANCE CURVES $\left(\mathrm{T}_{\mathrm{J}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)


Figure 2. $\mathrm{V}_{\text {drop }}$ vs. $\mathrm{I}_{\mathrm{L}} @ \mathrm{~V}_{\text {in }}=2.5 \mathrm{~V}$


Figure 4. On-Resistance vs. Input Voltage


Figure 6. Normalized On-Resistance Variation with Temperature


Figure 3. $\mathrm{V}_{\text {drop }}$ vs. $\mathrm{I}_{\mathrm{L}} @ \mathrm{~V}_{\mathrm{in}}=4.5 \mathrm{~V}$


Figure 5. On-Resistance Variation with Temperature


Figure 7. Switching Variation R2 @ $\mathrm{V}_{\mathrm{in}}=4.5 \mathrm{~V}, \mathrm{R} 1=20 \mathrm{k} \Omega$

TYPICAL PERFORMANCE CURVES $\left(\mathrm{T}_{J}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)


Figure 8. Switching Variation R2 @ $\mathrm{V}_{\mathrm{in}}=4.5 \mathrm{~V}, \mathrm{R} 1=20 \mathrm{k} \Omega$


Figure 10. Switching Variation


Figure 11. FET Thermal Response

## NTJD1155L

## PACKAGE DIMENSIONS

SC-88 (SOT-363)
CASE 419B-02
ISSUE W


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH,
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

|  | MILLIMETERS |  |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |  |
| A | 0.80 | 0.95 | 1.10 | 0.031 | 0.037 | 0.043 |  |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |  |
| A3 | 0.20 REF |  |  | 0.008 REF |  |  |  |
| b | 0.10 | 0.21 | 0.30 | 0.004 | 0.008 | 0.012 |  |
| C | 0.10 | 0.14 | 0.25 | 0.004 | 0.005 | 0.010 |  |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |  |
| E | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |  |
| e | 0.65 BSC |  |  |  | 0.026 BSC |  |  |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |  |
| $\mathbf{H}_{\mathbf{E}}$ | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |  |

STYLE 30:
PIN 1. SOURCE
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

SOLDERING FOOTPRINT*


SC-88/SC70-6/SOT363
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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[^0]:    1. Surface-mounted on FR4 board using 1 inch sq pad size
[^1]:    *Minimum R1 value should be at least $10 \times$ R2 to ensure Q1 turn-on.

